ABSTRACT OF THE DISCLOSURE

The intensity of the light emitted from the light-emitting diode 201 on wafer 105 is measured and then the potential difference between the terminals of the light-emitting element, and the plasma current flowing thereinto are derived from measured light intensity. Since the use of a camera enables non-contact measurement of emitted light intensity, the lead-in terminals for lead wires that are always required in conventional probing methods become unnecessary. In addition, since the target wafer does not require lead wire connection, wafers can be changed in the same way as performed for etching.